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Understanding [Embedded - FPGAs \(Field Programmable Gate Array\)](#)

Embedded - FPGAs, or Field Programmable Gate Arrays, are advanced integrated circuits that offer unparalleled flexibility and performance for digital systems. Unlike traditional fixed-function logic devices, FPGAs can be programmed and reprogrammed to execute a wide array of logical operations, enabling customized functionality tailored to specific applications. This reprogrammability allows developers to iterate designs quickly and implement complex functions without the need for custom hardware.

Applications of Embedded - FPGAs

The versatility of Embedded - FPGAs makes them indispensable in numerous fields. In telecommunications.

Details

Product Status	Active
Number of LABs/CLBs	-
Number of Logic Elements/Cells	-
Total RAM Bits	73728
Number of I/O	290
Number of Gates	300000
Voltage - Supply	2.3V ~ 2.7V
Mounting Type	Surface Mount
Operating Temperature	-55°C ~ 125°C (TC)
Package / Case	456-BBGA
Supplier Device Package	456-PBGA (35x35)
Purchase URL	https://www.e-xfl.com/product-detail/microchip-technology/apa300-bg456m

Device Resources

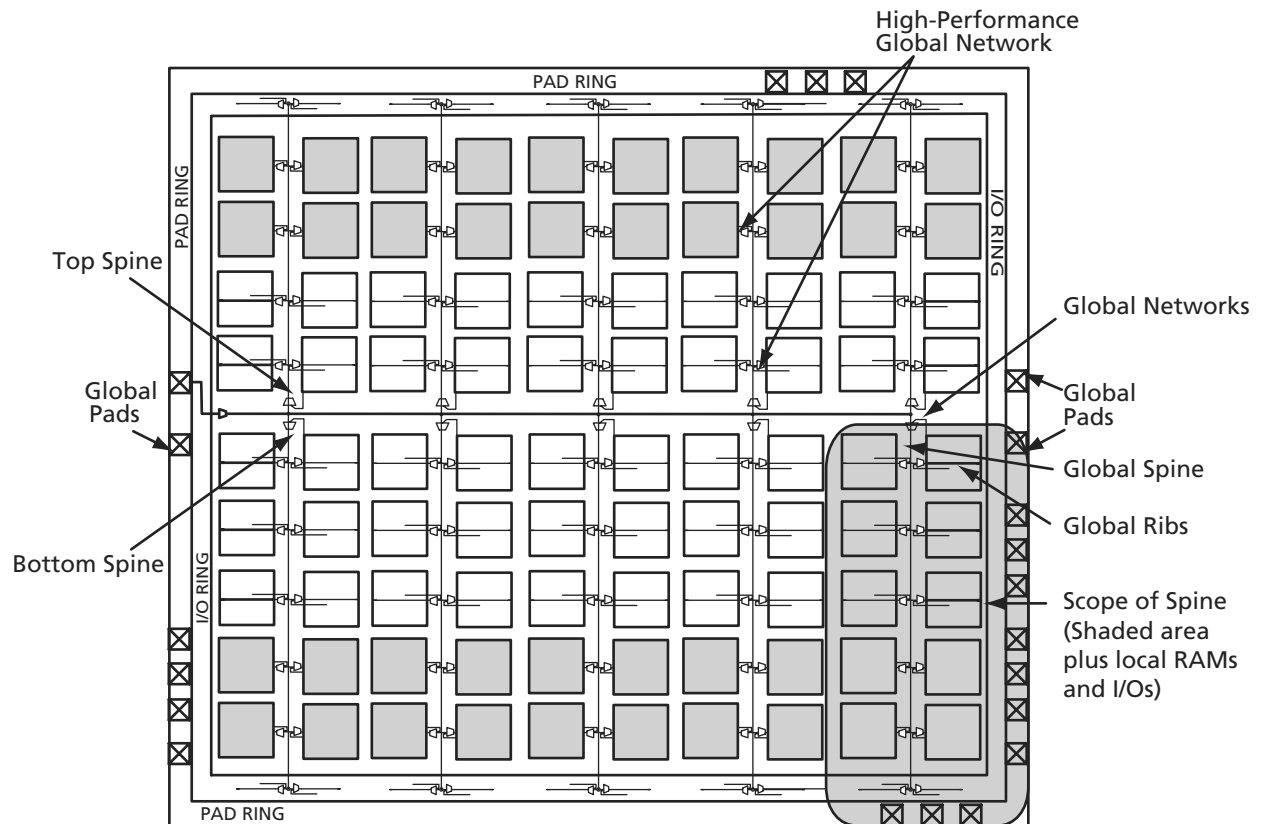
User I/Os ²													
Commercial/Industrial											Military/MIL-STD-883B		
Device	TQFP 100-Pin	TQFP 144-Pin	PQFP 208-Pin	PBGA 456-Pin	FBGA 144-Pin	FBGA 256-Pin	FBGA 484-Pin	FBGA 676-Pin	FBGA 896-Pin	FBGA 1152-Pin	CQFP 208-Pin	CQFP 352-Pin	CCGA/ LGA 624-Pin
APA075	66	107	158		100								
APA150	66		158	242	100	186 ³							
APA300			158 ⁴	290 ⁴	100 ⁴	186 ^{3,4}					158	248	
APA450			158	344	100	186 ³	344 ³						
APA600			158 ⁴	356 ⁴		186 ^{3,4}	370 ³	454			158	248	440
APA750			158	356				454	562 ⁵				
APA1000			158 ⁴	356 ⁴					642 ^{4,5}	712 ⁵	158	248	440

Notes:

1. Package Definitions: TQFP = Thin Quad Flat Pack, PQFP = Plastic Quad Flat Pack, PBGA = Plastic Ball Grid Array, FBGA = Fine Pitch Ball Grid Array, CQFP = Ceramic Quad Flat Pack, CCGA = Ceramic Column Grid Array, LGA = Land Grid Array
2. Each pair of PECL I/Os is counted as one user I/O.
3. FG256 and FG484 are footprint-compatible packages.
4. Military Temperature Plastic Package Offering
5. FG896 and FG1152 are footprint-compatible packages.

General Guideline

Maximum performance numbers in this datasheet are based on characterized data. Actel does not guarantee performance beyond the limits specified within the datasheet.



Note: This figure shows routing for only one global path.

Figure 1-7 • High-Performance Global Network

Table 1-1 • Clock Spines

	APA075	APA150	APA300	APA450	APA600	APA750	APA1000
Global Clock Networks (Trees)	4	4	4	4	4	4	4
Clock Spines/Tree	6	8	8	12	14	16	22
Total Spines	24	32	32	48	56	64	88
Top or Bottom Spine Height (Tiles)	16	24	32	32	48	64	80
Tiles in Each Top or Bottom Spine	512	768	1,024	1,024	1,536	2,048	2,560
Total Tiles	3,072	6,144	8,192	12,288	21,504	32,768	56,320

The TAP controller receives two control inputs (TMS and TCK) and generates control and clock signals for the rest of the test logic architecture. On power-up, the TAP controller enters the Test-Logic-Reset state. To guarantee a reset of the controller from any of the possible states, TMS must remain high for five TCK cycles. The TRST pin may also be used to asynchronously place the TAP controller in the Test-Logic-Reset state.

ProASIC^{PLUS} devices support three types of test data registers: bypass, device identification, and boundary scan. The bypass register is selected when no other register needs to be accessed in a device. This speeds up test data transfer to other devices in a test data path. The 32-bit device identification register is a shift register

with four fields (lowest significant byte (LSB), ID number, part number and version). The boundary-scan register observes and controls the state of each I/O pin.

Each I/O cell has three boundary-scan register cells, each with a serial-in, serial-out, parallel-in, and parallel-out pin. The serial pins are used to serially connect all the boundary-scan register cells in a device into a boundary-scan register chain, which starts at the TDI pin and ends at the TDO pin. The parallel ports are connected to the internal core logic tile and the input, output, and control ports of an I/O buffer to capture and load data into the register to control or observe the logic state of each I/O.

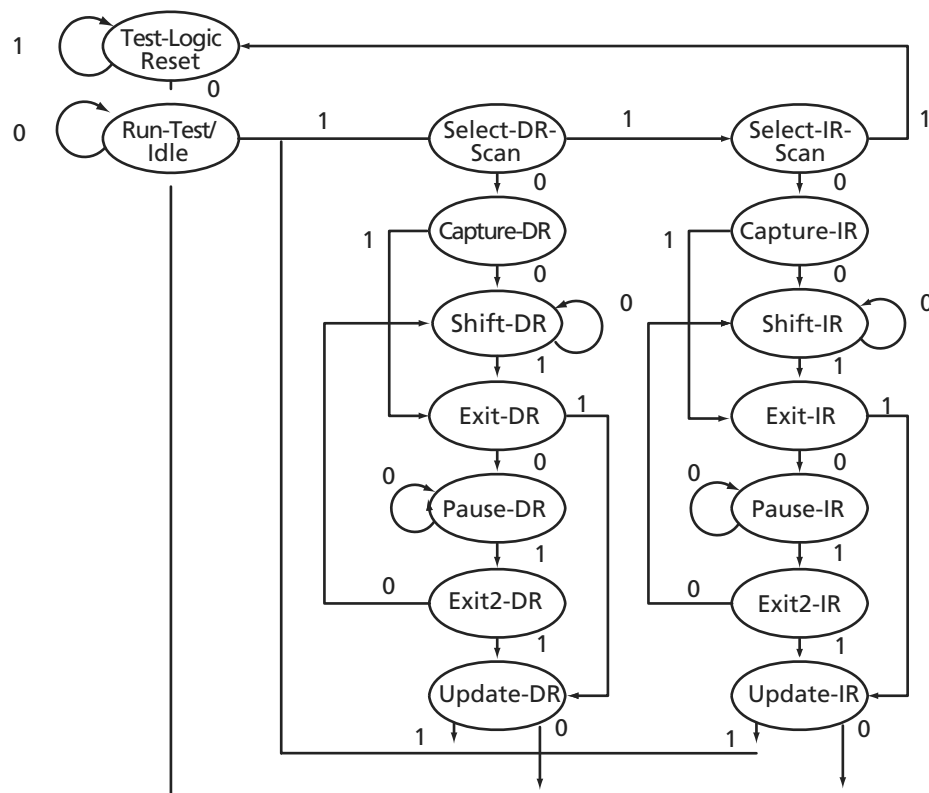


Figure 1-13 • TAP Controller State Diagram

Timing Control and Characteristics

ProASIC^{PLUS} Clock Management System

ProASIC^{PLUS} devices provide designers with very flexible clock conditioning capabilities. Each member of the ProASIC^{PLUS} family contains two phase-locked loop (PLL) blocks which perform the following functions:

- Clock Phase Adjustment via Programmable Delay (250 ps steps from -7 ns to +8 ns)
- Clock Skew Minimization
- Clock Frequency Synthesis

Each PLL has the following key features:

- Input Frequency Range (f_{IN}) = 1.5 to 180 MHz
- Feedback Frequency Range (f_{VCO}) = 24 to 180 MHz
- Output Frequency Range (f_{OUT}) = 8 to 180 MHz
- Output Phase Shift = 0 ° and 180 °
- Output Duty Cycle = 50%
- Low Output Jitter (max at 25°C)
 - $f_{VCO} < 10$ MHz. Jitter $\pm 1\%$ or better
 - $10 \text{ MHz} < f_{VCO} < 60$ MHz. Jitter $\pm 2\%$ or better
 - $f_{VCO} > 60$ MHz. Jitter $\pm 1\%$ or better

Note: Jitter(ps) = Jitter(%) * period

For Example:

Jitter in picoseconds at 100 MHz = $0.01 * (1/100E6) = 100$ ps

- Maximum Acquisition Time = 80 μ s for $f_{VCO} > 40$ MHz
= 30 μ s for $f_{VCO} < 40$ MHz
- Low Power Consumption – 6.9 mW (max – analog supply) + 7.0 μ W/MHz (max – digital supply)

Physical Implementation

Each side of the chip contains a clock conditioning circuit based on a 180 MHz PLL block (Figure 1-14 on page 1-14). Two global multiplexed lines extend along each side of the chip to provide bidirectional access to the PLL on that side (neither MUX can be connected to the opposite side's PLL). Each global line has optional LVPECL input pads (described below). The global lines may be driven by either the LVPECL global input pad or the outputs from the PLL block, or both. Each global line can be driven by a different output from the PLL. Unused global pins can be configured as regular I/Os or left unconnected. They default to an input with pull-up. The two signals available to drive the global networks are as

follows (Figure 1-15 on page 1-15, Table 1-7 on page 1-15, and Table 1-8 on page 1-16):

Global A (secondary clock)

- Output from Global MUX A
- Conditioned version of PLL output (f_{OUT}) – delayed or advanced
- Divided version of either of the above
- Further delayed version of either of the above (0.25 ns, 0.50 ns, or 4.00 ns delay)¹

Global B

- Output from Global MUX B
- Delayed or advanced version of f_{OUT}
- Divided version of either of the above
- Further delayed version of either of the above (0.25 ns, 0.50 ns, or 4.00 ns delay)²

Functional Description

Each PLL block contains four programmable dividers as shown in Figure 1-14 on page 1-14. These allow frequency scaling of the input clock signal as follows:

- The n divider divides the input clock by integer factors from 1 to 32.
- The m divider in the feedback path allows multiplication of the input clock by integer factors ranging from 1 to 64.
- The two dividers together can implement any combination of multiplication and division resulting in a clock frequency between 24 and 180 MHz exiting the PLL core. This clock has a fixed 50% duty cycle.
- The output frequency of the PLL core is given by the formula EQ 1-1 (f_{REF} is the reference clock frequency):

$$f_{OUT} = f_{REF} * m/n$$

EQ 1-1

- The third and fourth dividers (u and v) permit the signals applied to the global network to each be further divided by integer factors ranging from 1 to 4.

The implementations shown in EQ2 and EQ3 enable the user to define a wide range of frequency multiplier and divisors.

$$f_{GLB} = m/(n*u)$$

EQ 1-2

$$f_{GLA} = m/(n*v)$$

EQ 1-3

1. This mode is available through the delay feature of the Global MUX driver.

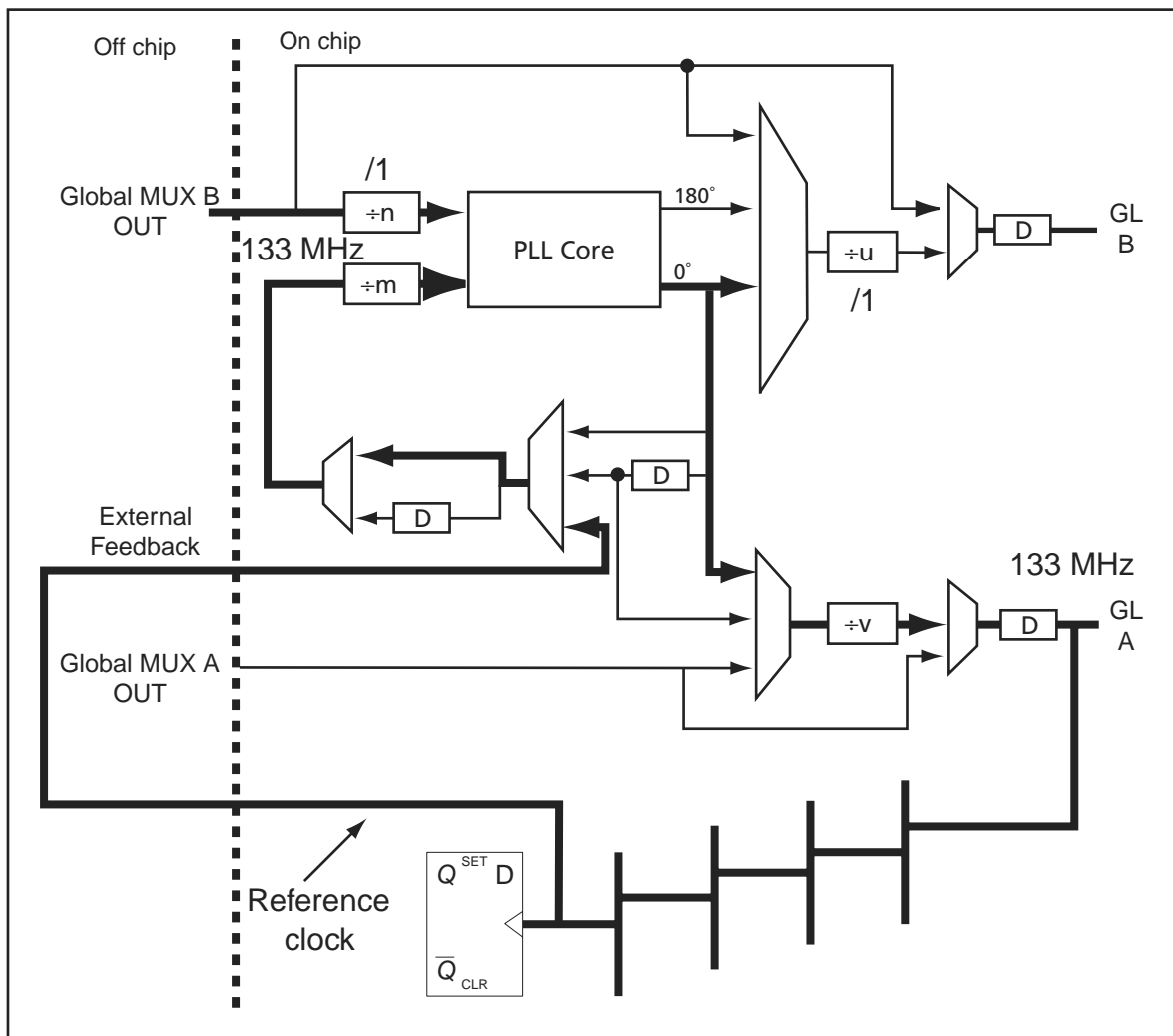


Figure 1-20 • Using the PLL for Clock Deskewing

Logic Tile Timing Characteristics

Timing characteristics for ProASIC^{PLUS} devices fall into three categories: family dependent, device dependent, and design dependent. The input and output buffer characteristics are common to all ProASIC^{PLUS} family members. Internal routing delays are device dependent. Design dependency means that actual delays are not determined until after placement and routing of the user's design are complete. Delay values may then be determined by using the Timer utility or by performing simulation with post-layout delays.

Critical Nets and Typical Nets

Propagation delays are expressed only for typical nets, which are used for initial design performance evaluation. Critical net delays can then be applied to the most timing-critical paths. Critical nets are determined by net property assignment prior to place-and-route. Refer to the Actel *Designer User's Guide* or online help for details on using constraints.

Table 1-9 • Temperature and Voltage Derating Factors
(Normalized to Worst-Case Commercial, $T_J = 70^\circ\text{C}$, $V_{DD} = 2.3\text{ V}$)

	-55°C	-40°C	0°C	25°C	70°C	85°C	110°C	125°C	135°C	150°C
2.3 V	0.84	0.86	0.91	0.94	1.00	1.02	1.05	1.13	1.18	1.27
2.5 V	0.81	0.82	0.87	0.90	0.95	0.98	1.01	1.09	1.13	1.21
2.7 V	0.77	0.79	0.83	0.86	0.91	0.93	0.96	1.04	1.08	1.16

Notes:

1. The user can set the junction temperature in Designer software to be any integer value in the range of -55°C to 175°C .
2. The user can set the core voltage in Designer software to be any value between 1.4 V and 1.6 V.

Timing Derating

Since ProASIC^{PLUS} devices are manufactured with a CMOS process, device performance will vary with temperature, voltage, and process. Minimum timing parameters reflect maximum operating voltage, minimum operating temperature, and optimal process variations. Maximum timing parameters reflect minimum operating voltage, maximum operating temperature, and worst-case process variations (within process specifications). The derating factors shown in Table 1-9 should be applied to all timing data contained within this datasheet.

All timing numbers listed in this datasheet represent sample timing characteristics of ProASIC^{PLUS} devices. Actual timing delay values are design-specific and can be derived from the Timer tool in Actel's Designer software after place-and-route.

PLL I/O Constraints

PLL locking is guaranteed only when the following constraints are followed:

Table 1-10 • PLL I/O Constraints

	T_J ≤ -40°C		Value T_J > -40°C
I/O Type	PLL locking is guaranteed only when using low drive strength and low slew rate I/O. PLL locking may be inconsistent when using high drive strength or high slew rate I/Os		No Constraints
SSO	APA300	Hermetic packages ≤ 8 SSO	With FIN ≤ 180 MHz and outputs switching simultaneously
		Plastic packages ≤ 16 SSO	
	APA600	Hermetic packages ≤ 16 SSO	
		Plastic packages ≤ 32 SSO	
	APA1000	Hermetic packages ≤ 16 SSO	With FIN ≤ 50 MHz and half outputs switching on positive clock edge, half switching on the negative clock edge no less than 10nsec later
		Plastic packages ≤ 32 SSO	
	APA300	Hermetic packages ≤ 12 SSO	
		Plastic packages ≤ 20 SSO	
	APA600	Hermetic packages ≤ 32 SSO	
		Plastic packages ≤ 64 SSO	
	APA1000	Hermetic packages ≤ 32 SSO	
		Plastic packages ≤ 64 SSO	

Logic-Tile Contribution— P_{logic}

P_{logic} , the logic-tile component of AC power dissipation, is given by

$$P_{logic} = P3 * mc * Fs$$

where:

- $P3$ = 1.4 μ W/MHz is the average power consumption of a logic tile per MHz of its output toggling rate. The maximum output toggling rate is $Fs/2$.
- mc = the number of logic tiles switching during each Fs cycle
- Fs = the clock frequency

I/O Output Buffer Contribution— $P_{outputs}$

$P_{outputs}$, the I/O component of AC power dissipation, is given by

$$P_{outputs} = (P4 + (C_{load} * V_{DDP}^2)) * p * Fp$$

where:

- $P4$ = 326 μ W/MHz is the intrinsic power consumption of an output pad normalized per MHz of the output frequency. This is the total I/O current V_{DDP} .
- C_{load} = the output load
- p = the number of outputs
- Fp = the average output frequency

I/O Input Buffer's Buffer Contribution— P_{inputs}

The input's component of AC power dissipation is given by

$$P_{inputs} = P8 * q * Fq$$

where:

- $P8$ = 29 μ W/MHz is the intrinsic power consumption of an input pad normalized per MHz of the input frequency.
- q = the number of inputs
- Fq = the average input frequency

PLL Contribution— P_{pll}

$$P_{pll} = P9 * N_{pll}$$

where:

- $P9$ = 7.5 mW. This value has been estimated at maximum PLL clock frequency.
- N_{pll} = number of PLLs used

RAM Contribution— P_{memory}

Finally, P_{memory} , the memory component of AC power consumption, is given by

$$P_{memory} = P6 * N_{memory} * F_{memory} * E_{memory}$$

where:

- $P6$ = 175 μ W/MHz is the average power consumption of a memory block per MHz of the clock
- N_{memory} = the number of RAM/FIFO blocks
(1 block = 256 words * 9 bits)
- F_{memory} = the clock frequency of the memory
- E_{memory} = the average number of active blocks divided by the total number of blocks (N) of the memory.
 - Typical values for E_{memory} would be 1/4 for a 1k x 8,9,16, 32 memory and 1/16 for a 4kx8, 9, 16, and 32 memory configuration
 - In addition, an application-dependent component to E_{memory} can be considered. For example, for a 1kx8 memory configuration using only 1 cycle out of 2, $E_{memory} = 1/4 * 1/2 = 1/8$

Table 1-22 • DC Electrical Specifications ($V_{DDP} = 2.5 \text{ V} \pm 0.2\text{V}$)

Symbol	Parameter	Conditions		Commercial/Industrial/ Military/MIL-STD-883 ^{1, 2}			Units
				Min.	Typ.	Max.	
V _{OH}	Output High Voltage High Drive (OB25LPH)	I _{OH} = –6 mA	2.1			V	
		I _{OH} = –12 mA	2.0				
		I _{OH} = –24 mA	1.7				
	Low Drive (OB25LPL)	I _{OH} = –3 mA	2.1				
		I _{OH} = –6 mA	1.9				
		I _{OH} = –8 mA	1.7				
V _{OL}	Output Low Voltage High Drive (OB25LPH)	I _{OL} = 8 mA			0.2	V	
		I _{OL} = 15 mA			0.4		
		I _{OL} = 24 mA			0.7		
	Low Drive (OB25LPL)	I _{OL} = 4 mA			0.2		
		I _{OL} = 8 mA			0.4		
		I _{OL} = 15 mA			0.7		
V _{IH} ⁶	Input High Voltage		1.7		V _{DDP} + 0.3	V	
V _{IL} ⁷	Input Low Voltage		–0.3		0.7	V	
R _{WEAKPULLUP}	Weak Pull-up Resistance (OTB25LPU)	V _{IN} ≥ 1.25 V		6		56	kΩ
HYST	Input Hysteresis Schmitt	See Table 1-4 on page 1-9		0.3	0.35	0.45	V
I _{IN}	Input Current	with pull up (V _{IN} = GND)		–240		– 20	μA
		without pull up (V _{IN} = GND or V _{DD})		–10		10	μA
I _{DDQ}	Quiescent Supply Current (standby) Commercial	V _{IN} = GND ⁴ or V _{DD}	Std.		5.0	15	mA
			–F ³		5.0	25	mA
I _{DDQ}	Quiescent Supply Current (standby) Industrial	V _{IN} = GND ⁴ or V _{DD}	Std.		5.0	20	mA
I _{DDQ}	Quiescent Supply Current (standby) Military/MIL-STD-883	V _{IN} = GND ⁴ or V _{DD}	Std.		5.0	25	mA
I _{OZ}	Tristate Output Leakage Current	V _{OH} = GND or V _{DD}	Std.	–10		10	μA
			–F ^{3, 5}	–10		100	μA

Notes:

1. All process conditions. Commercial/Industrial: Junction Temperature: -40 to $+110^\circ\text{C}$.
2. All process conditions. Military: Junction Temperature: -55 to $+150^\circ\text{C}$.
3. All -F parts are available only as commercial.
4. No pull-up resistor.
5. This will not exceed 2 mA total per device.
6. During transitions, the input signal may overshoot to $V_{DDP} + 1.0\text{V}$ for a limited time of no larger than 10% of the duty cycle.
7. During transitions, the input signal may undershoot to -1.0V for a limited time of no larger than 10% of the duty cycle.

Table 1-22 • DC Electrical Specifications ($V_{DDP} = 2.5\text{ V} \pm 0.2\text{V}$) (Continued)

Symbol	Parameter	Conditions	Commercial/Industrial/ Military/MIL-STD-883 ^{1, 2}			Units
			Min.	Typ.	Max.	
I_{OSH}	Output Short Circuit Current High High Drive (OB25LPH) Low Drive (OB25LPL)	$V_{IN} = V_{SS}$ $V_{IN} = V_{SS}$	-120 -100			mA
I_{OSL}	Output Short Circuit Current Low High Drive (OB25LPH) Low Drive (OB25LPL)	$V_{IN} = V_{DDP}$ $V_{IN} = V_{DDP}$			100 30	mA
$C_{I/O}$	I/O Pad Capacitance				10	pF
C_{CLK}	Clock Input Pad Capacitance				10	pF

Notes:

1. All process conditions. Commercial/Industrial: Junction Temperature: -40 to $+110^{\circ}\text{C}$.
2. All process conditions. Military: Junction Temperature: -55 to $+150^{\circ}\text{C}$.
3. All -F parts are available only as commercial.
4. No pull-up resistor.
5. This will not exceed 2 mA total per device.
6. During transitions, the input signal may overshoot to $V_{DDP} + 1.0\text{V}$ for a limited time of no larger than 10% of the duty cycle.
7. During transitions, the input signal may undershoot to -1.0V for a limited time of no larger than 10% of the duty cycle.

Table 1-24 • **DC Electrical Specifications ($V_{DDP} = 3.3 \text{ V} \pm 0.3 \text{ V}$ and $V_{DD} = 2.5 \text{ V} \pm 0.2 \text{ V}$) (Continued)**
Applies to Military Temperature and MIL-STD-883B Temperature Only

Symbol	Parameter	Conditions		Military/MIL-STD-883B ¹			Units
				Min.	Typ.	Max.	
I_{DDQ}	Quiescent Supply Current (standby) Industrial	$V_{IN} = \text{GND}^2$ or V_{DD}	Std.		5.0	20	mA
I_{DDQ}	Quiescent Supply Current (standby) Military	$V_{IN} = \text{GND}^2$ or V_{DD}	Std.		5.0	25	mA
I_{OZ}	Tristate Output Leakage Current	$V_{OH} = \text{GND}$ or V_{DD}	Std.	–10		10	μA
			–F ³	–10		100	μA
I_{OSH}	Output Short Circuit Current High 3.3 V High Drive (OB33P) 3.3 V Low Drive (OB33L)	$V_{IN} = \text{GND}$ $V_{IN} = \text{GND}$		–200 –100			
I_{OSL}	Output Short Circuit Current Low 3.3 V High Drive 3.3 V Low Drive	$V_{IN} = V_{DD}$ $V_{IN} = V_{DD}$				200 100	
$C_{I/O}$	I/O Pad Capacitance					10	pF
C_{CLK}	Clock Input Pad Capacitance					10	pF

Notes:

1. All process conditions. Military Temperature / MIL-STD-883 Class B: Junction Temperature: -55 to $+125^\circ\text{C}$.
2. No pull-up resistor required.
3. This will not exceed 2 mA total per device.
4. During transitions, the input signal may overshoot to $V_{DDP} + 1.0 \text{ V}$ for a limited time of no larger than 10% of the duty cycle.
5. During transitions, the input signal may undershoot to -1.0 V for a limited time of no larger than 10% of the duty cycle.

Table 1-37 • Worst-Case Military Conditions

 $V_{DDP} = 3.0V$, $V_{DD} = 2.3V$, $T_J = 125^{\circ}C$ for Military/MIL-STD-883

Macro Type	Description	Max. t_{INYH} ¹	Max. t_{INYL} ²	Units
		Std.	Std.	
IB33	3.3V, CMOS Input Levels ³ , No Pull-up Resistor	0.5	0.6	ns
IB33S	3.3V, CMOS Input Levels ³ , No Pull-up Resistor, Schmitt Trigger	0.6	0.8	ns

Notes:

1. t_{INYH} = Input Pad-to-Y High
2. t_{INYL} = Input Pad-to-Y Low
3. LVTTL delays are the same as CMOS delays.
4. For LP Macros, $V_{DDP}=2.3V$ for delays.

Table 1-38 • Worst-Case Military Conditions

 $V_{DDP} = 2.3V$, $V_{DD} = 2.3V$, $T_J = 125^{\circ}C$ for Military/MIL-STD-883

Macro Type	Description	Max. t_{INYH} ¹	Max. t_{INYL} ²	Units
		Std.	Std.	
IB25LP	2.5V, CMOS Input Levels ³ , Low Power	0.9	0.7	ns
IB25LPS	2.5V, CMOS Input Levels ³ , Low Power, Schmitt Trigger	0.8	1.0	ns

Notes:

1. t_{INYH} = Input Pad-to-Y High
2. t_{INYL} = Input Pad-to-Y Low
3. LVTTL delays are the same as CMOS delays.
4. For LP Macros, $V_{DDP}=2.3V$ for delays.

Table 1-41 • Worst-Case Military Conditions

 $V_{DDP} = 3.0V$, $V_{DD} = 2.3V$, $T_J = 125^{\circ}C$ for Military/MIL-STD-883

Macro Type	Description	Max. t_{INYH} ¹	Max. t_{INYL} ²
		Std.	Std.
GL33	3.3V, CMOS Input Levels ³ , No Pull-up Resistor	1.1	1.1
GL33S	3.3V, CMOS Input Levels ³ , No Pull-up Resistor, Schmitt Trigger	1.1	1.1
PECL	PPECL Input Levels	1.1	1.1

Notes:

1. t_{INYH} = Input Pad-to-Y High
2. t_{INYL} = Input Pad-to-Y Low
3. LVTTTL delays are the same as CMOS delays.
4. For LP Macros, $V_{DDP}=2.3V$ for delays.

Table 1-42 • Worst-Case Military Conditions

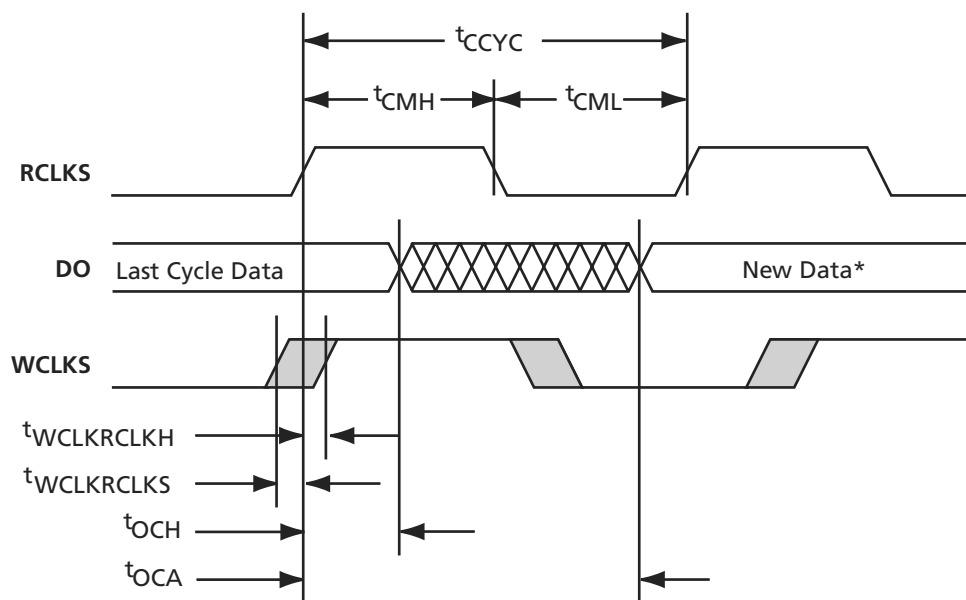
 $V_{DDP} = 2.3V$, $V_{DD} = 2.3V$, $T_J = 125^{\circ}C$ for Military/MIL-STD-883

Macro Type	Description	Max. t_{INYH} ¹	Max. t_{INYL} ²
		Std.	Std.
GL25LP	2.5V, CMOS Input Levels ³ , Low Power	1.0	1.1
GL25LPS	2.5V, CMOS Input Levels ³ , Low Power, Schmitt Trigger	1.4	1.0

Notes:

1. t_{INYH} = Input Pad-to-Y High
2. t_{INYL} = Input Pad-to-Y Low
3. LVTTTL delays are the same as CMOS delays.
4. For LP Macros, $V_{DDP}=2.3V$ for delays.

Synchronous Write and Read to the Same Location



* New data is read if WCLKS ↑ occurs before setup time.
The data stored is read if WCLKS ↑ occurs after hold time.

Note: The plot shows the normal operation status.

Figure 1-37 • Synchronous Write and Read to the Same Location

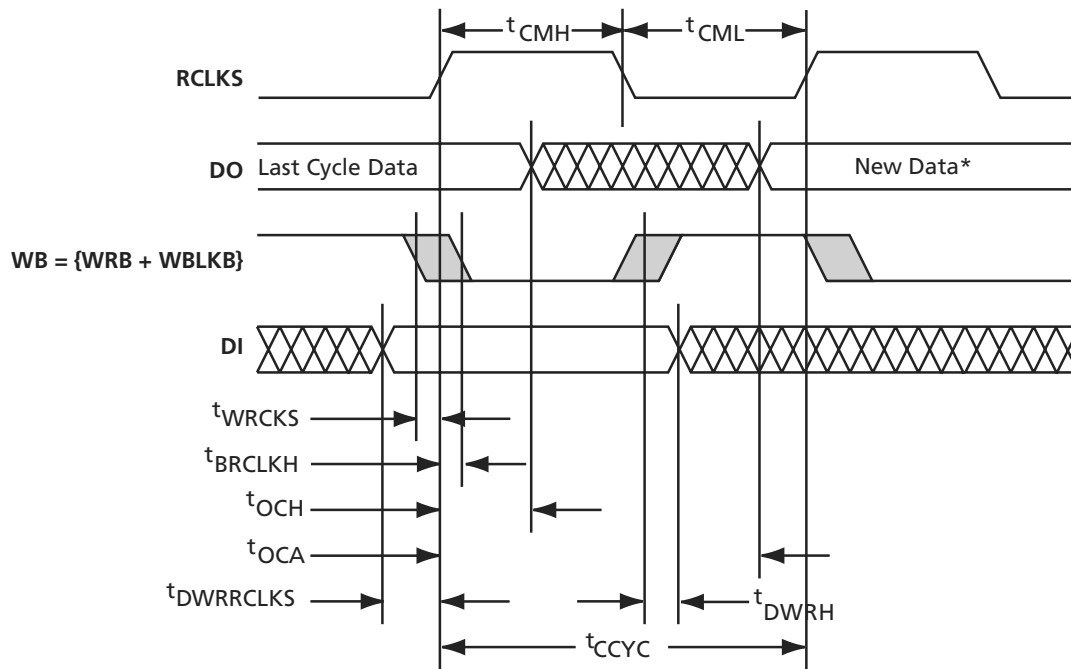
Table 1-58 • $T_J = 0^\circ\text{C}$ to 110°C ; $V_{DD} = 2.3\text{ V}$ to 2.7 V for Commercial/industrial
 $T_J = -55^\circ\text{C}$ to 150°C , $V_{DD} = 2.3\text{ V}$ to 2.7 V for Military/MIL-STD-883

Symbol t_{xxx}	Description	Min.	Max.	Units	Notes
CCYC	Cycle time	7.5		ns	
CMH	Clock high phase	3.0		ns	
CML	Clock low phase	3.0		ns	
WCLKRCLKS	WCLKS ↑ to RCLKS ↑ setup time	-0.1		ns	
WCLKRCLKH	WCLKS ↑ to RCLKS ↑ hold time		7.0	ns	
OCH	Old DO valid from RCLKS ↑		3.0	ns	OCA/OCH displayed for Access Timed Output
OCA	New DO valid from RCLKS ↑	7.5		ns	

Notes:

1. This behavior is valid for Access Timed Output and Pipelined Mode Output. The table shows the timings of an Access Timed Output.
2. During synchronous write and synchronous read access to the same location, the new write data will be read out if the active write clock edge occurs before or at the same time as the active read clock edge. The negative setup time insures this behavior for WCLKS and RCLKS driven by the same design signal.
3. If WCLKS changes after the hold time, the data will be read.
4. A setup or hold time violation will result in unknown output data.
5. All -F speed grade devices are 20% slower than the standard numbers.

Asynchronous Write and Synchronous Read to the Same Location



* New data is read if WB ↓ occurs before setup time.
The stored data is read if WB ↓ occurs after hold time.

Note: The plot shows the normal operation status.

Figure 1-38 • Asynchronous Write and Synchronous Read to the Same Location

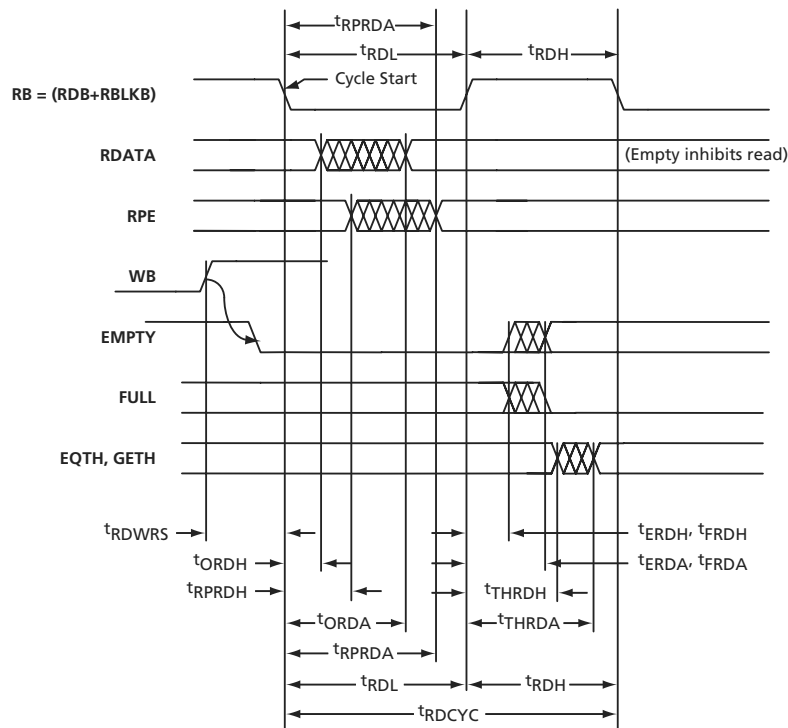
Table 1-59 • $T_J = 0^\circ\text{C}$ to 110°C ; $V_{DD} = 2.3\text{ V}$ to 2.7 V for Commercial/industrial
 $T_J = -55^\circ\text{C}$ to 150°C , $V_{DD} = 2.3\text{ V}$ to 2.7 V for Military/MIL-STD-883

Symbol t_{xxx}	Description	Min.	Max.	Units	Notes
CCYC	Cycle time	7.5		ns	
CMH	Clock high phase	3.0		ns	
CML	Clock low phase	3.0		ns	
WBRCCLKS	WB ↓ to RCLKS ↑ setup time	-0.1		ns	
WBRCCLKH	WB ↓ to RCLKS ↑ hold time		7.0	ns	
OCH	Old DO valid from RCLKS ↑		3.0	ns	OCA/OCH displayed for Access Timed Output
OCA	New DO valid from RCLKS ↑	7.5		ns	
DWRRCLKS	DI to RCLKS ↑ setup time	0		ns	
DWRH	DI to WB ↑ hold time		1.5	ns	

Notes:

1. This behavior is valid for Access Timed Output and Pipelined Mode Output. The table shows the timings of an Access Timed Output.
2. In asynchronous write and synchronous read access to the same location, the new write data will be read out if the active write signal edge occurs before or at the same time as the active read clock edge. If WB changes to low after hold time, the data will be read.
3. A setup or hold time violation will result in unknown output data.
4. All -F speed grade devices are 20% slower than the standard numbers.

Asynchronous FIFO Read



Note: The plot shows the normal operation status.

Figure 1-43 • Asynchronous FIFO Read

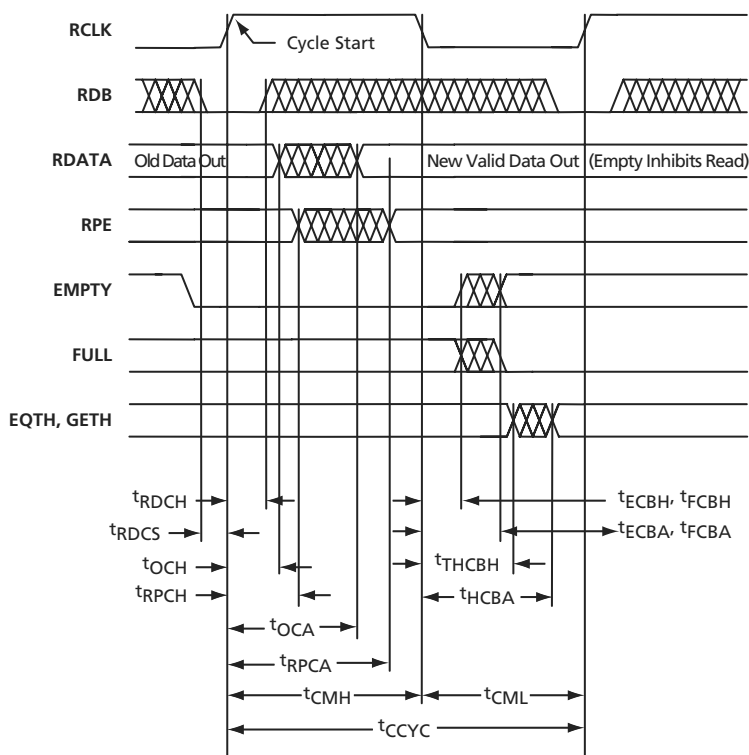
Table 1-63 • $T_J = 0^\circ\text{C}$ to 110°C ; $V_{DD} = 2.3\text{ V}$ to 2.7 V for Commercial/industrial
 $T_J = -55^\circ\text{C}$ to 150°C , $V_{DD} = 2.3\text{ V}$ to 2.7 V for Military/MIL-STD-883

Symbol t_{xxx}	Description	Min.	Max.	Units	Notes
ERDH, FRDH, THRDH	Old EMPTY, FULL, EQTH, & GETH valid hold time from RB \uparrow		0.5	ns	Empty/full/thresh are invalid from the end of hold until the new access is complete
ERDA	New EMPTY access from RB \uparrow	3.0 ¹		ns	
FRDA	FULL \downarrow access from RB \uparrow	3.0 ¹		ns	
ORDA	New DO access from RB \downarrow	7.5		ns	
ORDH	Old DO valid from RB \downarrow		3.0	ns	
RDCYC	Read cycle time	7.5		ns	
RDWRS	WB \uparrow , clearing EMPTY, setup to RB \downarrow	3.0 ²		ns	Enabling the read operation
			1.0	ns	Inhibiting the read operation
RDH	RB high phase	3.0		ns	Inactive
RDL	RB low phase	3.0		ns	Active
RPRDA	New RPE access from RB \downarrow	9.5		ns	
RPRDH	Old RPE valid from RB \downarrow		4.0	ns	
THRDA	EQTH or GETH access from RB \uparrow	4.5		ns	

Notes:

- At fast cycles, $ERDA$ and $FRDA = \text{MAX}(7.5\text{ ns} - RDL), 3.0\text{ ns}$.
- At fast cycles, $RDWRS$ (for enabling read) = $\text{MAX}(7.5\text{ ns} - WRL), 3.0\text{ ns}$.
- All -F speed grade devices are 20% slower than the standard numbers.

Synchronous FIFO Read, Access Timed Output Strobe (Synchronous Transparent)



Note: The plot shows the normal operation status.

Figure 1-45 • Synchronous FIFO Read, Access Timed Output Strobe (Synchronous Transparent)

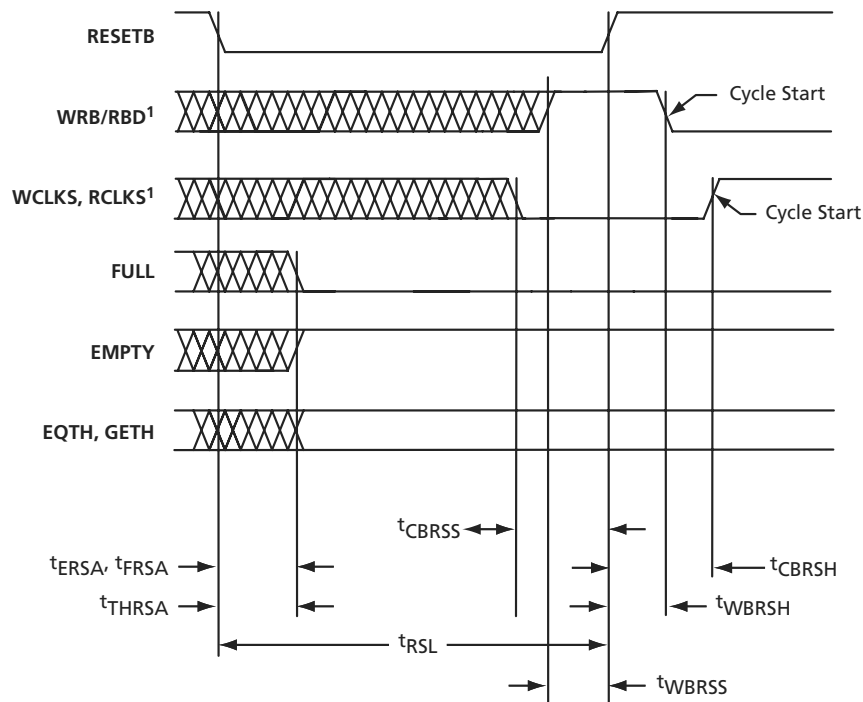
Table 1-65 • $T_J = 0^\circ\text{C}$ to 110°C ; $V_{DD} = 2.3\text{ V}$ to 2.7 V for Commercial/industrial
 $T_J = -55^\circ\text{C}$ to 150°C , $V_{DD} = 2.3\text{ V}$ to 2.7 V for Military/MIL-STD-883

Symbol t_{xxx}	Description	Min.	Max.	Units	Notes
CCYC	Cycle time	7.5		ns	
CMH	Clock high phase	3.0		ns	
CML	Clock low phase	3.0		ns	
ECBA	New EMPTY access from RCLKS ↓	3.0 ¹		ns	
FCBA	FULL ↓ access from RCLKS ↓	3.0 ¹		ns	
ECBH, FCBH, THCBH	Old EMPTY, FULL, EQTH, & GETH valid hold time from RCLKS ↓		1.0	ns	Empty/full/thresh are invalid from the end of hold until the new access is complete
OCA	New DO access from RCLKS ↑	7.5		ns	
OCH	Old DO valid from RCLKS ↑		3.0	ns	
RDCH	RDB hold from RCLKS ↑	0.5		ns	
RDCS	RDB setup to RCLKS ↑	1.0		ns	
RPCA	New RPE access from RCLKS ↑	9.5		ns	
RPCH	Old RPE valid from RCLKS ↑		3.0	ns	
HCBA	EQTH or GETH access from RCLKS ↓	4.5		ns	

Notes:

- At fast cycles, ECBA and FCBA = MAX (7.5 ns – CMH), 3.0 ns.
- All –F speed grade devices are 20% slower than the standard numbers.

FIFO Reset



Notes:

- During reset, either the enables (WRB and RBD) OR the clocks (WCLKS and RCLKS) must be low.
- The plot shows the normal operation status.

Figure 1-48 • FIFO Reset

Table 1-68 • $T_J = 0^\circ\text{C}$ to 110°C ; $V_{DD} = 2.3\text{ V}$ to 2.7 V for Commercial/industrial
 $T_J = -55^\circ\text{C}$ to 150°C , $V_{DD} = 2.3\text{ V}$ to 2.7 V for Military/MIL-STD-883

Symbol t_{xxx}	Description	Min.	Max.	Units	Notes
CBRSH ¹	WCLKS or RCLKS \uparrow hold from RESETB \uparrow	1.5		ns	Synchronous mode only
CBRSS ¹	WCLKS or RCLKS \downarrow setup to RESETB \uparrow	1.5		ns	Synchronous mode only
ERSA	New EMPTY \uparrow access from RESETB \downarrow	3.0		ns	
FRSA	FULL \downarrow access from RESETB \downarrow	3.0		ns	
RSL	RESETB low phase	7.5		ns	
THRSA	EQTH or GETH access from RESETB \downarrow	4.5		ns	
WBRSH ¹	WB \downarrow hold from RESETB \uparrow	1.5		ns	Asynchronous mode only
WBRSS ¹	WB \uparrow setup to RESETB \uparrow	1.5		ns	Asynchronous mode only

Notes:

- During reset, the enables (WRB and RBD) must be high OR the clocks (WCLKS and RCLKS) must be low.
- All -F speed grade devices are 20% slower than the standard numbers.

Pin Description

User Pins

I/O User Input/Output

The I/O pin functions as an input, output, tristate, or bidirectional buffer. Input and output signal levels are compatible with standard LVTTTL and LVCMOS specifications. Unused I/O pins are configured as inputs with pull-up resistors.

NC No Connect

To maintain compatibility with other Actel ProASIC^{PLUS} products, it is recommended that this pin not be connected to the circuitry on the board.

GL Global Pin

Low skew input pin for clock or other global signals. This pin can be configured with an internal pull-up resistor. When it is not connected to the global network or the clock conditioning circuit, it can be configured and used as a normal I/O.

GLMX Global Multiplexing Pin

Low skew input pin for clock or other global signals. This pin can be used in one of two special ways (refer to Actel's *Using ProASIC^{PLUS} Clock Conditioning Circuits*).

When the external feedback option is selected for the PLL block, this pin is routed as the external feedback source to the clock conditioning circuit.

In applications where two different signals access the same global net at different times through the use of GLMXx and GLMXLx macros, this pin will be fixed as one of the source pins.

This pin can be configured with an internal pull-up resistor. When it is not connected to the global network or the clock conditioning circuit, it can be configured and used as any normal I/O. If not used, the GLMXx pin will be configured as an input with pull-up.

Dedicated Pins

GND Ground

Common ground supply voltage.

V_{DD} Logic Array Power Supply Pin

2.5 V supply voltage.

V_{DDP} I/O Pad Power Supply Pin

2.5 V or 3.3 V supply voltage.

TMS Test Mode Select

The TMS pin controls the use of boundary-scan circuitry. This pin has an internal pull-up resistor.

TCK Test Clock

Clock input pin for boundary scan (maximum 10 MHz). Actel recommends adding a nominal 20 kΩ pull-up resistor to this pin.

TDI Test Data In

Serial input for boundary scan. A dedicated pull-up resistor is included to pull this pin high when not being driven.

TDO Test Data Out

Serial output for boundary scan. Actel recommends adding a nominal 20kΩ pull-up resistor to this pin.

TRST Test Reset Input

Asynchronous, active-low input pin for resetting boundary-scan circuitry. This pin has an internal pull-up resistor. For more information, please refer to *Power-up Behavior of ProASIC^{PLUS} Devices* application note.

Special Function Pins

RCK Running Clock

A free running clock is needed during programming if the programmer cannot guarantee that TCK will be uninterrupted. If not used, this pin has an internal pull-up and can be left floating.

NPECL User Negative Input

Provides high speed clock or data signals to the PLL block. If unused, leave the pin unconnected.

PPECL User Positive Input

Provides high speed clock or data signals to the PLL block. If unused, leave the pin unconnected.

AVDD PLL Power Supply

Analog V_{DD} should be V_{DD} (core voltage) 2.5 V (nominal) and be decoupled from GND with suitable decoupling capacitors to reduce noise. For more information, refer to Actel's *Using ProASIC^{PLUS} Clock Conditioning Circuits* application note. If the clock conditioning circuitry is not used in a design, AVDD can either be left floating or tied to 2.5 V.

AGND PLL Power Ground

The analog ground can be connected to the system ground. For more information, refer to Actel's *Using ProASIC^{PLUS} Clock Conditioning Circuits* application note. If the PLLs or clock conditioning circuitry are not used in a design, AGND should be tied to GND.